

FDH210N08 N-Channel UniFETTM MOSFET **75 V, 210 A, 5.5 m**Ω

Features

- $R_{DS(on)}$ = 4.65 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 125 A
- Low Gate Charge (Typ. 232 nC)
- Low C_{rss} (Typ. 262 pF)
- · 100% Avalanche Tested
- · Improved dv/dt Capability

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies

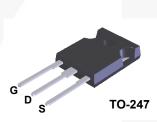
December 2013

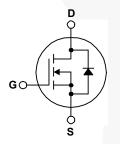


FDH210N08 — N-Channel UniFETTM MOSFET

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDH210N08	Unit
V _{DSS}	Drain-Source Voltage		75	V
ID	Drain Current - Continuous ($T_C = 25^{\circ}C$)		210	А
	- Continuous (T _C = 10	0 ^o C)	132	A
I _{DM}	Drain Current - Pulsed	(Note 1)	840	A
V _{GSS}	Gate-Source Voltage		± 20	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	9375	mJ
I _{AR}	Avalanche Current	(Note 1)	210	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	46.2	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		462	W
	- Derate Above 25°C		3.7	W/ºC
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	MaximumLead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FDH210N08	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.27	°C/W	
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

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— N-Channel
UniFET TM
MOSFET

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDH210N08	FDH210N08	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

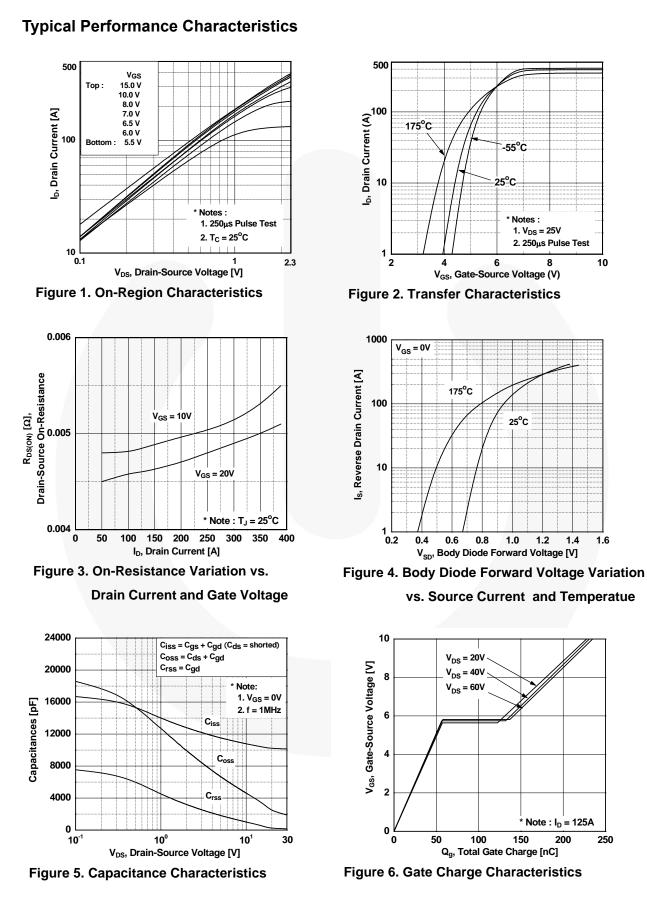
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	75			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25° C		0.1		V/ºC
I _{DSS} Zero Gate V	Zero Gate Voltage Drain Current	V _{DS} = 75 V, V _{GS} = 0 V			20	μA
		$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 150^{\circ}\text{C}$			250	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			200	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-200	nA
On Charac	teristics				1	1
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 125 A		4.65	5.5	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 25 V, I _D = 125 A		200		S
Dynamic C	Characteristics					I.
C _{iss}	Input Capacitance			8743	11340	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		2134	2778	pF
C _{rss}	Reverse Transfer Capacitance	-1 = 1.0 IVITIZ		262	393	pF
Switching	Characteristics		-	I		
t _{d(on)}	Turn-On Delay Time			100	210	ns
t _r	Turn-On Rise Time	$V_{DD} = 37.5 \text{ V}, \text{ I}_{D} = 69 \text{ A},$		410	830	ns
t _{d(off)}	Turn-Off Delay Time	$-R_{G} = 25 \Omega$		630	1270	ns
t _f	Turn-Off Fall Time	(Note 4)		290	590	ns
Qg	Total Gate Charge			232	301	nC
Q _{gs}	Gate-Source Charge	$V_{DS} = 60 \text{ V}, \text{ I}_{D} = 125 \text{ A},$		58		nC
Q _{gd}	Gate-Drain Charge	- V _{GS} = 10 V (Note 4)		77		nC
Drain-Sour	rce Diode Characteristics and Maximum Rat	ings				
Is Maximum Continuous Drain-Source Diode Forward Current				210	А	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				840	А
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 125 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 125 A,		123		ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 \text{ A}/\mu\text{s}$		420		nC

Notes:

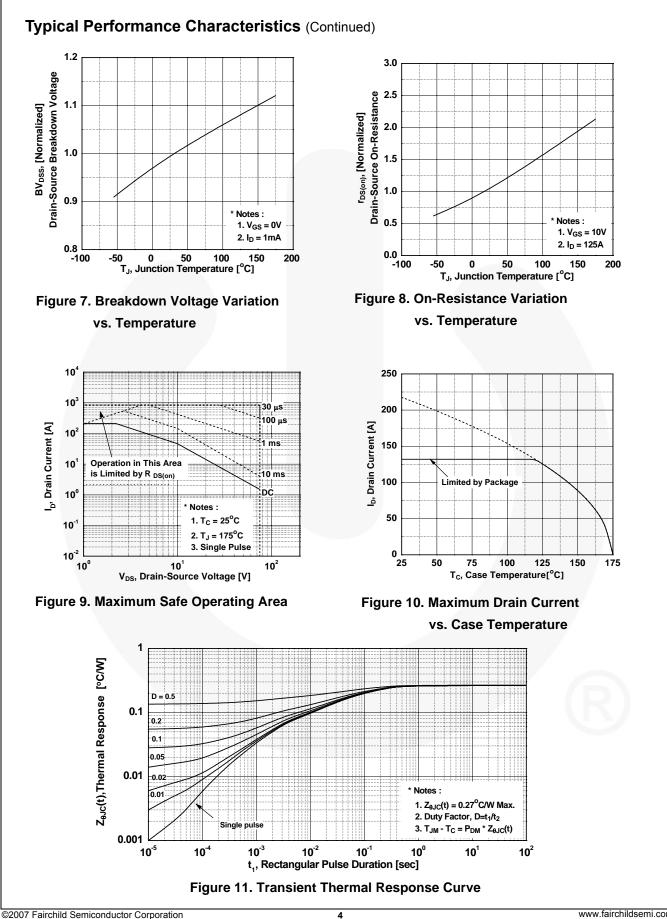
1. Repetitive rating: pulse-width limited by maximum junction temperature.

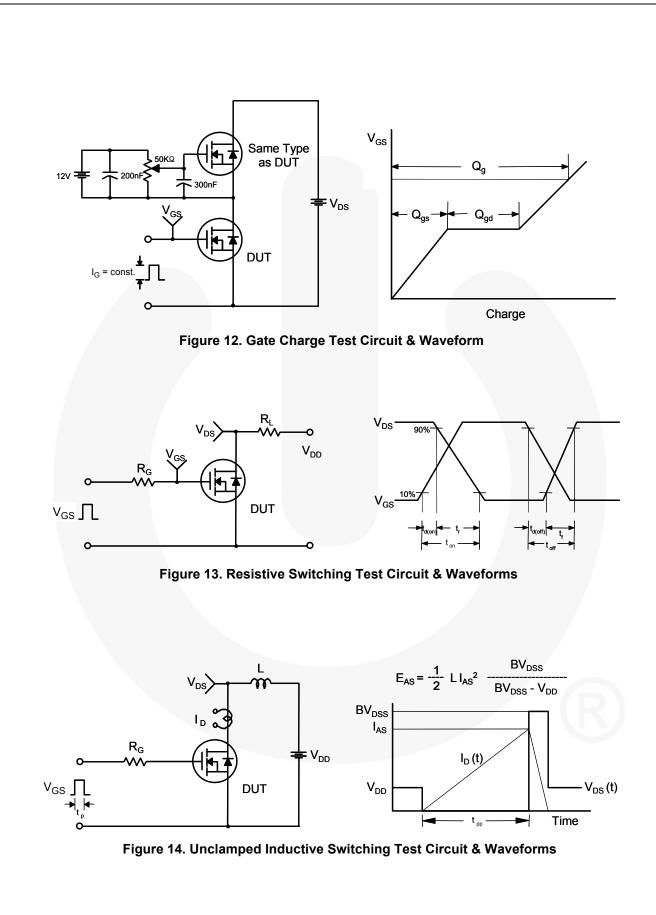
2.L = 0.4 mH, I_{AS} = 125 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. $I_{SD} \le 125$ A, di/dt ≤ 260 A/µs, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.

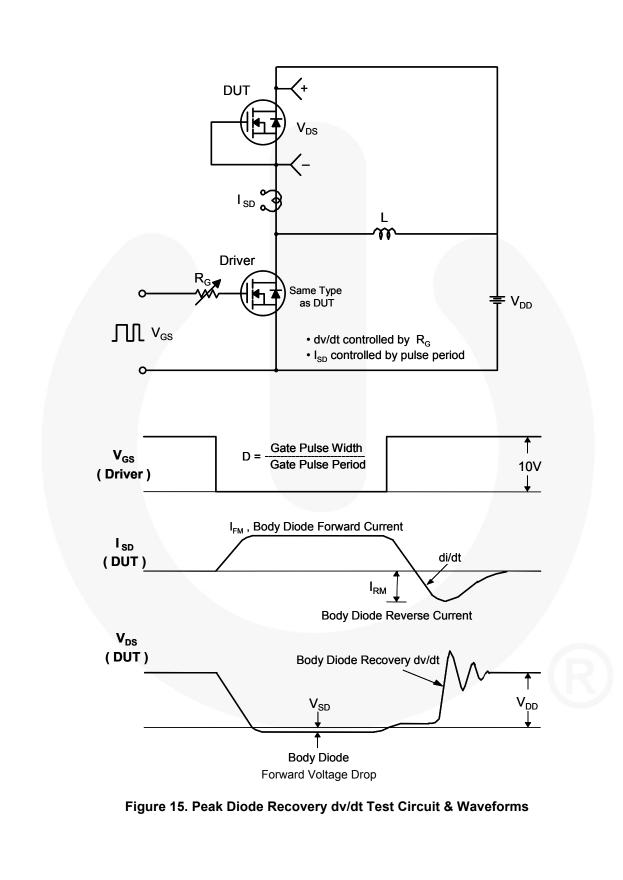
4. Essentially independent of operating temperature typical characteristics.

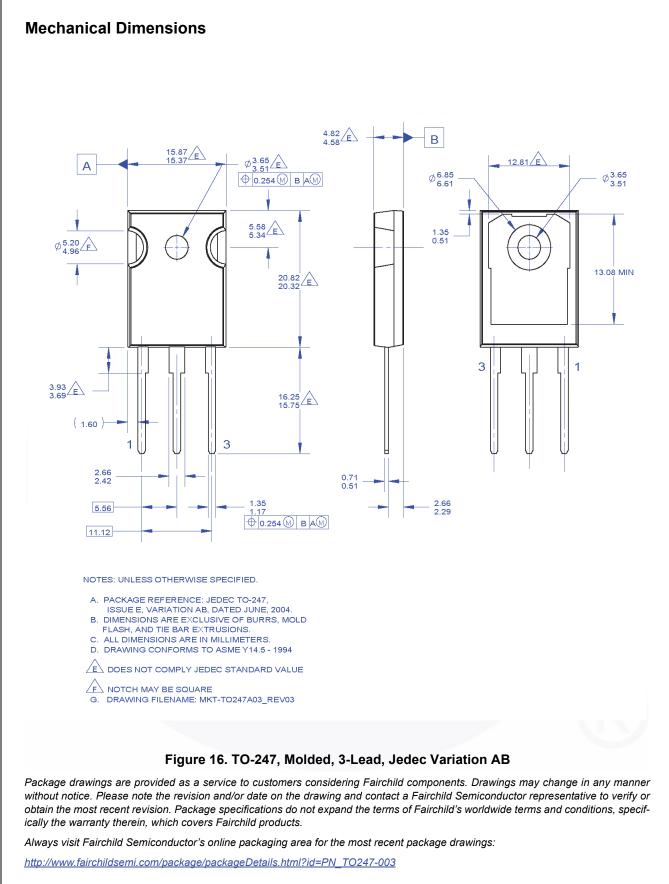


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